NTS10120EMFS, NRVTS10120EMFS

Very Low Leakage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing Diodes
- Reverse Battery Protection
- LED Lighting
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

1

• Device Meets MSL 1 Requirements



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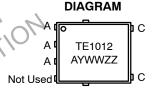
http://onsemi.com

TRENCH SCHOTTKY RECTIFIERS 10 AMPERES 120 VOLTS

1,2,3 0 5,6



SO-8 FLAT LEAD CASE 488AA STYLE 2



MARKING

TE1012 = Specific Device Code A = Assembly Location Y = Year

W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTS10120EMFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTS10120EMFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVTS10120EMFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVTS10120EMFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	120	V	
Average Rectified Forward Current (Rated V_R , T_C = 165°C)	I _{F(AV)}	10	А	
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, $T_C = 163^{\circ}C$)	I _{FRM}	20	Α	
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	200	А	
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Operating Junction Temperature	TJ	-55 to +175	°C	
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E _{AS}	100	mJ	
ESD Rating (Human Body Model)		3B	7	
ESD Rating (Machine Model)		M4 S		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic		Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)		R _{eJC}	2 1.8	<u> </u>	°C/W

ELECTRICAL CHARACTERISTICS

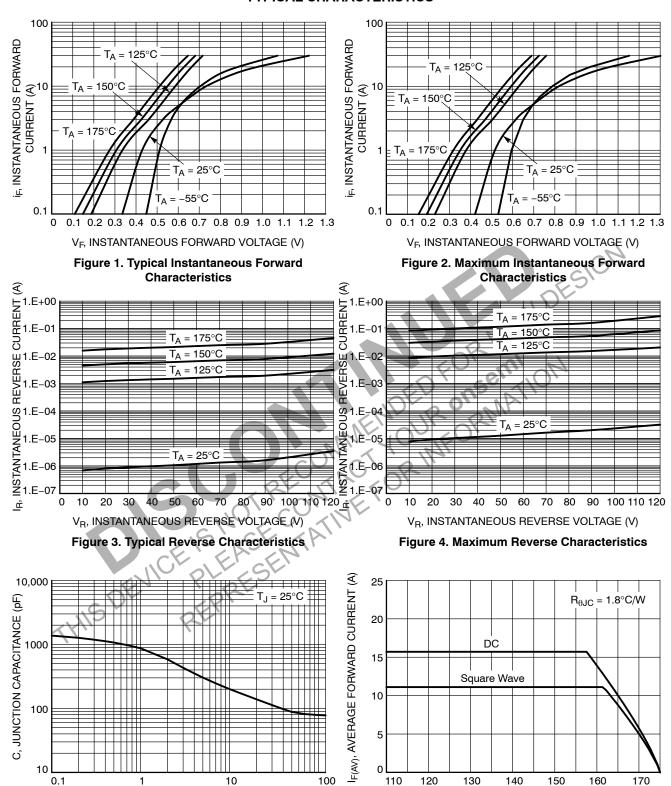
Rating	Symbol	Тур	Max	Unit
Instantaneous Forward Voltage (Note 1)	V_{F}			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.6	_	
$(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$		0.735	0.82	
		0.545		
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.515	_	
$(I_F = 10 \text{ A}, T_J = 125^{\circ}\text{C})$		0.588	0.63	
Instantaneous Reverse Current (Note 1)	I _R			
$(V_R = 90 \text{ V}, T_J = 25^{\circ}\text{C})$		1.0	_	μΑ
(Rated dc Voltage, T _J = 25°C)		3.75	30	μΑ
0E 102 P				
$(V_R = 90 \text{ V}, T_J = 125^{\circ}\text{C})$		2.0	_	mA
(Rated dc Voltage, T _J = 125°C)		3.1	20	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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TYPICAL CHARACTERISTICS



 $\label{eq:VR} V_R,\, \text{REVERSE VOLTAGE (V)}$ Figure 5. Typical Junction Capacitance

T_C, CASE TEMPERATURE (°C) Figure 6. Current Derating

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TYPICAL CHARACTERISTICS

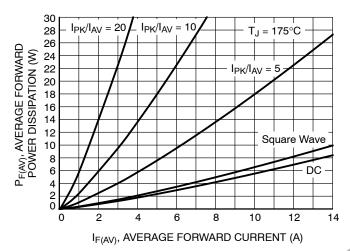


Figure 7. Forward Power Dissipation

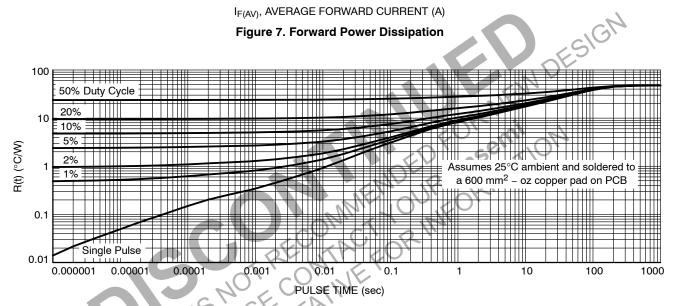


Figure 8. Typical Thermal Characteristics

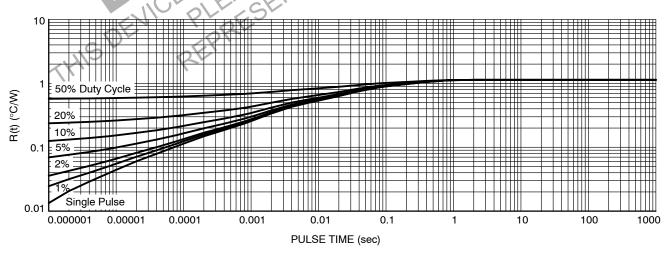


Figure 9. Typical Transient Thermal Response Characteristics, Junction-to-Case





0.10

SIDE VIEW

DFN5 5x6, 1.27P (SO-8FL) CASE 488AA ISSUE N

DATE 25 JUN 2018

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETER. DIMENSION D1 AND E1 DO NOT INCLUDE
- MOLD FLASH PROTRUSIONS OR GATE BURRS

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.90	1.00	1.10	
A1	0.00		0.05	
b	0.33	0.41	0.51	
С	0.23	0.28	0.33	
D	5.00	5.15	5.30	
D1	4.70	4.90	5.10	
D2	3.80	4.00	4.20	
E	6.00	6.15	6.30	
E1	5.70	5.90	6.10	
E2	3.45	3.65	3.85	
е		1.27 BSC		
G	0.51	0.575	0.71	
K	1.20	1.35	1.50	
L	0.51	0.575	0.71	
L1	0.125 REF			
M	3.00	3.40	3.80	
θ	0 °		12 °	

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code

= Lot Traceability

= Assembly Location Α

Υ = Year W = Work Week

ZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.





DETAIL A

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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